ESD/TLP Measurement Iustruments and ESD Immunity Anaiysis in the Electronic Device

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ABSTRACT

Reliability engineer of integrated circuit occupies a most important position when the accuracy of process got better and better . The improvement of the technical procedure will enhance the reliability of integrated circuit in design. There is another element to effect the reliability engineer when we enhances the yield. Though one of the factors is the ESD of destruction.it can be avoidable. There are many productions of the protection circuit of ESD in academic.but ESD protect the circuit and some elements which protect the circuit are often effected by the efficiency of ESD stress cause the circuit protection is useless. The reliable of the circuit protection element is queried. The thesis will use some ESD protection Devices to do ESP testing. Analyze anti ESD ability. Pick up element to avoid latch up effect . To analyze the reliable ability and ESD energy. we can use the TLP and ESD instruments which is similar to ESD stress to test the anti-static electricity ability. Prote element can maintain the voltage effectively. When the element of voltage value enter the collapse point effectively and maintain appropriate capacity of releasing the ESD. Furthermore, it also prevent the coming of second collapse point effectively. Therefore how to find and the first and second appropriate collapse point is very impertant. Analyzing the static electricity workable or not in a circuit.

Keywords : Reliability.collapose point

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